

SILICON NPN PHOTO DETECTOR

DESCRIPTION:

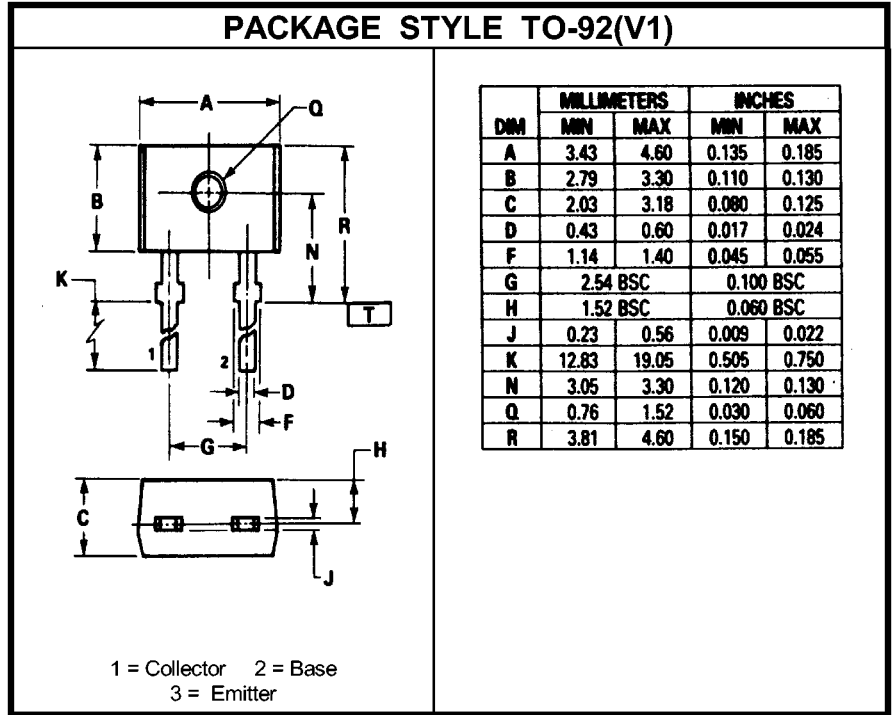
The **2N5777(MOD.)** is Designed for General Purpose Industrial Photo Detector Applications.

FEATURES:

- High Sensitivity
- Economical TO-92 compatible package

MAXIMUM RATINGS

I_L	250 mA
V_{CEO}	40 V
P_{DISS}	250 mW @ T _C = 25 °C
T_J	-40 to +100 °C
T_{ST}	-40 to +100 °C


CHARACTERISTICS T_A = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
I _D	I _C = 1 mA	40	60		V
I _L	V _{CE} = 12 V			100	nA
	V _{CE} = 5 V H = 500 μW/cm ²	5			mA
C _{CE}	V _{CE} = 10 V f = 1 MHz		3.2		pF
V _{CE(sat)}	V _{CE} = 5 V I _C = 2 mA H = 500 μW/cm ²		0.75	1.0	V
t _{on}	V _{CE} = 10 V R _L = 100 Ω H = 500 μW/cm ²		125		μS
t _{off}	V _{CE} = 10 V R _L = 100 Ω H = 500 μW/cm ²		150		μS